

SHEET 1 OF 1

INFORMATION DISCLOSURE CITATION PTO-1449		CUSTOMER NUMBER 45114	ATTORNEY'S DKT NO. H1102C	APPLICATION NO. 10/720,166
			APPLICANT(S) Shibly S. Ahmed et al.	
			FILING DATE November 25, 2003	GROUP 2822

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
MW	2005/0104091	05/2005	Tabery et al.	257	213	

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER	<i>M.W. Iczewski</i>	DATE CONSIDERED	<i>10/2005</i>
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).

INFORMATION DISCLOSURE CITATION PTO-1449	CUSTOMER NUMBER 26615	ATTORNEY'S DKT No. H1102C	APPLICATION NO. 10/720,166
		APPLICANT(s) Shibly S. AHMED et al.	
		FILING DATE November 25, 2003	GROUP <i>Unassigned</i> <i>d 828</i>

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>MW</i>	6,583,469 B1	06/24/2003	Fried et al.	257	329	
<i>MW</i>	6,525,403 B2	02/25/2003	Inaba et al.	257	618	
<i>MW</i>	6,551,885 B1	04/22/2003	Yu	438	300	
<i>MW</i>	5,960,270	09/28/1999	Misra et al.	438	197	
<i>MW</i>	6,515,320 B1	02/04/2003	Azuma et al.	257	288	
<i>MW</i>	6,303,447 B1	10/16/2001	Chhagan et al.	438	299	
<i>MW</i>	6,342,410 B1	01/29/2002	Yu	438	164	
<i>MW</i>	6,265,256 B1	07/24/2001	An et al.	438	201	
<i>MW</i>	6,413,802 B1	07/02/2002	Hu et al.	438	151	
<i>MW</i>	6,406,951 B1	06/18/2002	Yu	438	183	
<i>MW</i>	6,551,886 B1	04/22/2003	Yu	438	300	
<i>MW</i>	6,475,890 B1	11/05/2002	Yu	438	574	
<i>MW</i>	6,562,665 B1	05/13/2003	Yu	438	149	
<i>MW</i>	6,458,662 B1	10/01/2002	Yu	438	286	

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
<i>MW</i>	WO 03/015182 A2	02/20/2003	WO			Abstract Only	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>MW</i>	United States Patent Application Publication No. US 2003/0111686 A1; Publication Date: June 19, 2003; Nowak.
<i>MW</i>	United States Patent Application Publication No. US 2003/0141525 A1; Publication Date: July 31, 2003; Nowak
<i>MW</i>	United States Patent Application Publication No. US 2003/0113970 A1; Publication Date: June 19, 2003; Fried et al.
<i>MW</i>	United States Patent Application Publication No. US 2003/0151077 A1; Publication Date: August 14, 2003; Mathew et al.

EXAMINER	<i>Mukleczewski</i>	DATE CONSIDERED	<i>10/2005</i>
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INFORMATION DISCLOSURE CITATION <small>PTO-1449</small>		CUSTOMER NUMBER 26615	ATTORNEY'S DKT NO. H1102C	APPLICATION NO. 10/720,166		
			APPLICANT(S) Shibly S. AHMED et al.			
			FILING DATE November 25, 2003	GROUP Unassigned <i>2802</i>		
AN 08 2004 U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
FOREIGN PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation
						Yes
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)						
<i>MW</i>	Copy of co-pending Application Serial No. 10/645,577; entitled "Sacrificial Oxide Protection During Dummy Gate Removal in Damascene Gate Process in Semiconductor Devices; filed on August 22, 2003; 28 pages.					
<i>MW</i>	Copy of co-pending Application Serial No. 10/320,536; entitled "FinFET Gate Formation Using Reverse Trim of Dummy Gate"; filed on December 17, 2002; 25 pages.					
<i>MW</i>	Copy of co-pending Application Serial No. 10/459,589; entitled "FinFET Gate Formation Using Reverse Trim and Oxide Polish"; filed on June 12, 2003; 45 pages.					
<i>MW</i>	Digh Hisamoto et al., "FinFET-A Self-Aligned Double-Gate MOSFET Scalable to 20 nm," IEEE Transactions on Electron Devices, Vol. 47, No. 12, December 2000, pages 2320-2325.					
<i>MW</i>	Yang-Kyu Choi et al., "Sub-20nm CMOS FinFET Technologies," 2001 IEEE, IEDM, pages 421-424.					
<i>MW</i>	Xuejue Huang et al., "Sub-50 nm P-Channel FinFET," IEEE Transactions on Electron Devices, Vol. 48, No. 5, May 2001, pages 880-886.					
<i>MW</i>	Xuejue Huang et al., "Sub 50-nm FinFET: PMOS," 1999 IEEE, IEDM, pages 67-70.					
<i>MW</i>	Yang-Kyu Choi et al., "Nanoscale CMOS Spacer FinFET for the Terabit Era," IEEE Electron Device Letters, Vol. 23, No. 1, January 2002, pages 25-27.					
EXAMINER <i>MW/Wilczewski</i>	DATE CONSIDERED <i>10/2005</i>					

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			APPLICANT(S) Shibly S. AHMED et al.			
			FILING DATE November 25, 2003	GROUP Unassigned 0802		
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
FOREIGN PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation Yes No
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)						
<i>MW</i>	Copy of U.S. Serial No. 10/754,559; filed January 12, 2004; entitled: "DAMASCENE TRIGATE FINFET"; 28 pages.					
EXAMINER	<i>MW/czawski</i>			DATE CONSIDERED <i>10/2005</i>		

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INFORMATION
DISCLOSURE
CITATION
PTO-1449

CUSTOMER NUMBER	ATTORNEY'S Dkt No. H1102C	APPLICATION NO. 10/720,166
	APPLICANT(S) Shibly S. Ahmed et al.	
	FILING DATE November 25, 2003	GROUP 1756- 2822

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
MW	6,396,108	05/28/02	Krivokapic et al.	257	365	
MW	5,801,397	09/01/98	Cunningham	257	66	
MW	6,686,231	02/03/04	Ahmed et al.	438	164	

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

MW	Stephen H. Tang et al., "Comparison of Short-Channel Effect and Offstate Leakage in Symmetric vs. Asymmetric Double Gate MOSFETs", IEEE International SOI Conference, October 2000, pp. 120-121
MW	United States Patent Application Publication No. US2002/0153587; publication date October 24, 2002; Adkisson et al.

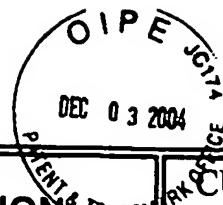
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INFORMATION DISCLOSURE CITATION PTO-1449 <i>JC13G</i> <i>MAY 6 2005</i> <i>U.S. PATENT & TRADEMARK OFFICE</i>		CUSTOMER NUMBER 45114	ATTORNEY'S DKT No. H1102C	APPLICATION NO. 10/720,166			
			APPLICANT(S) Shibly S. Ahmed et al.				
			FILING DATE November 25, 2003	GROUP 1756 <i>2822</i>			
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
<i>MW</i>	6,764,884B1	07/20/2004	Yu et al.	438	157		
<i>MW</i>	6,465,823B1	10/15/2002	Yagishita et al.	438	157		
<i>MW</i>	6,765,303B1	07/20/04	Krivokapic et al.	257	903		
<i>MW</i>	6,509,611B1	01/21/03	Park et al.	257	330		
<i>MW</i>	2002/0177263A1	11/28/02	Hanafi et al.	438	183		
<i>MW</i>	2002/0153587A1	10/24/02	Adkisson et al.	257	510		
FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
<i>MW</i>	EP 1 383 164 A1	01/21/04	Europe			Yes	No
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER	<i>MW/czewski</i>		DATE CONSIDERED <i>10/2005</i>				

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